

**MICROWAVE SEMICONDUCTOR
TECHNICAL DATA****TMD3438-1**

FEATURES

- Suitable for WLL Subscriber/CPE
- High Power P1dB=29dBm(min)
- High Gain G1dB=29dB(min)
- High Linearity

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

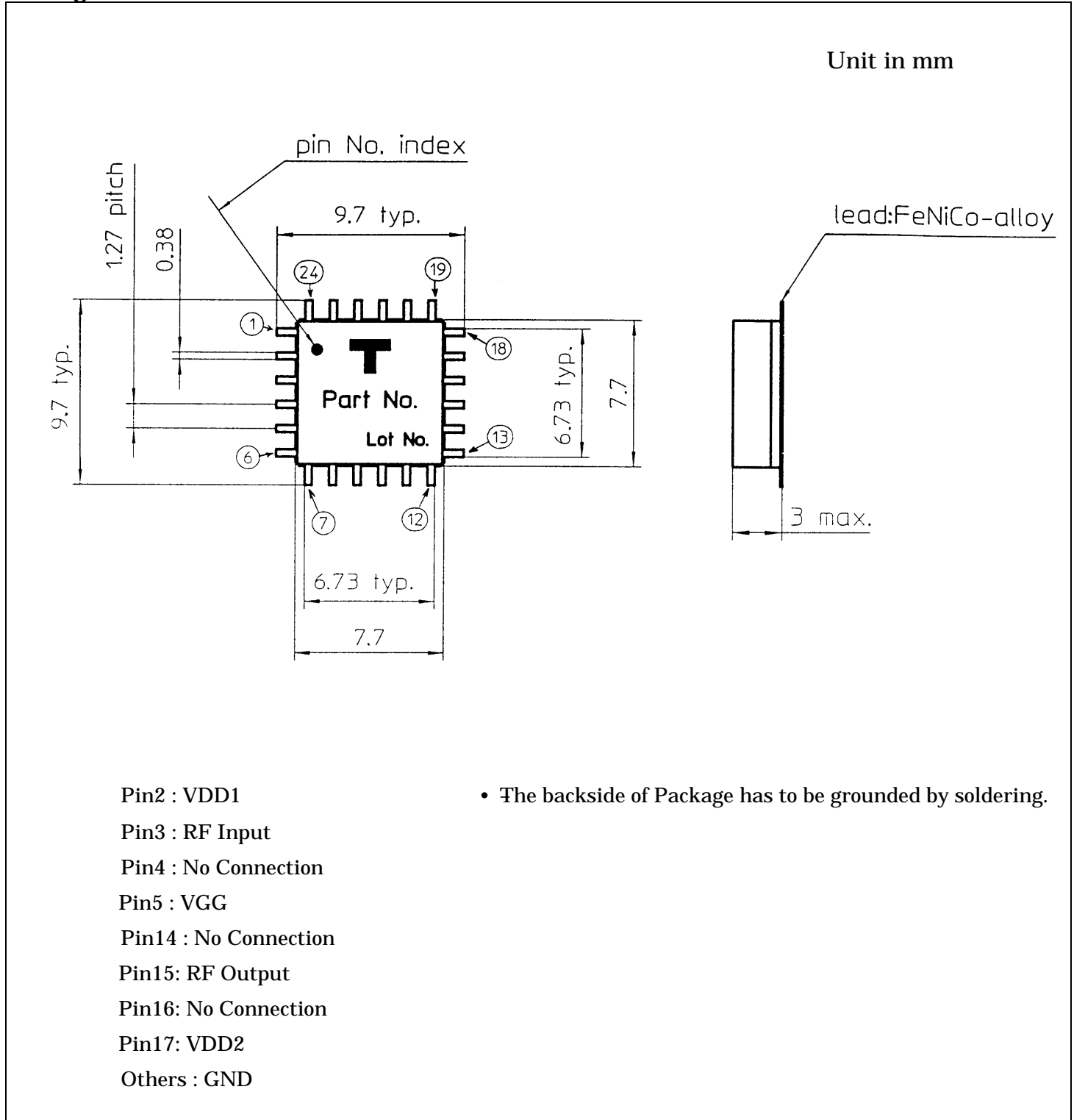
CHARACTERISTICS	SYMBOL	UNIT	RATINGS
Drain Supply Voltage	VDD	V	10
Gate Supply Voltage	VGG	V	-10
Input Power	Pin	dBm	10
Total Power Dissipation	PT	W	6
Flange Temperature	Tf	°C	-40 ~ +85
Storage Temperature	Tstg	°C	-65 ~ +150

RF PERFORMANCE SPECIFICATIONS (Ta=25 °C)

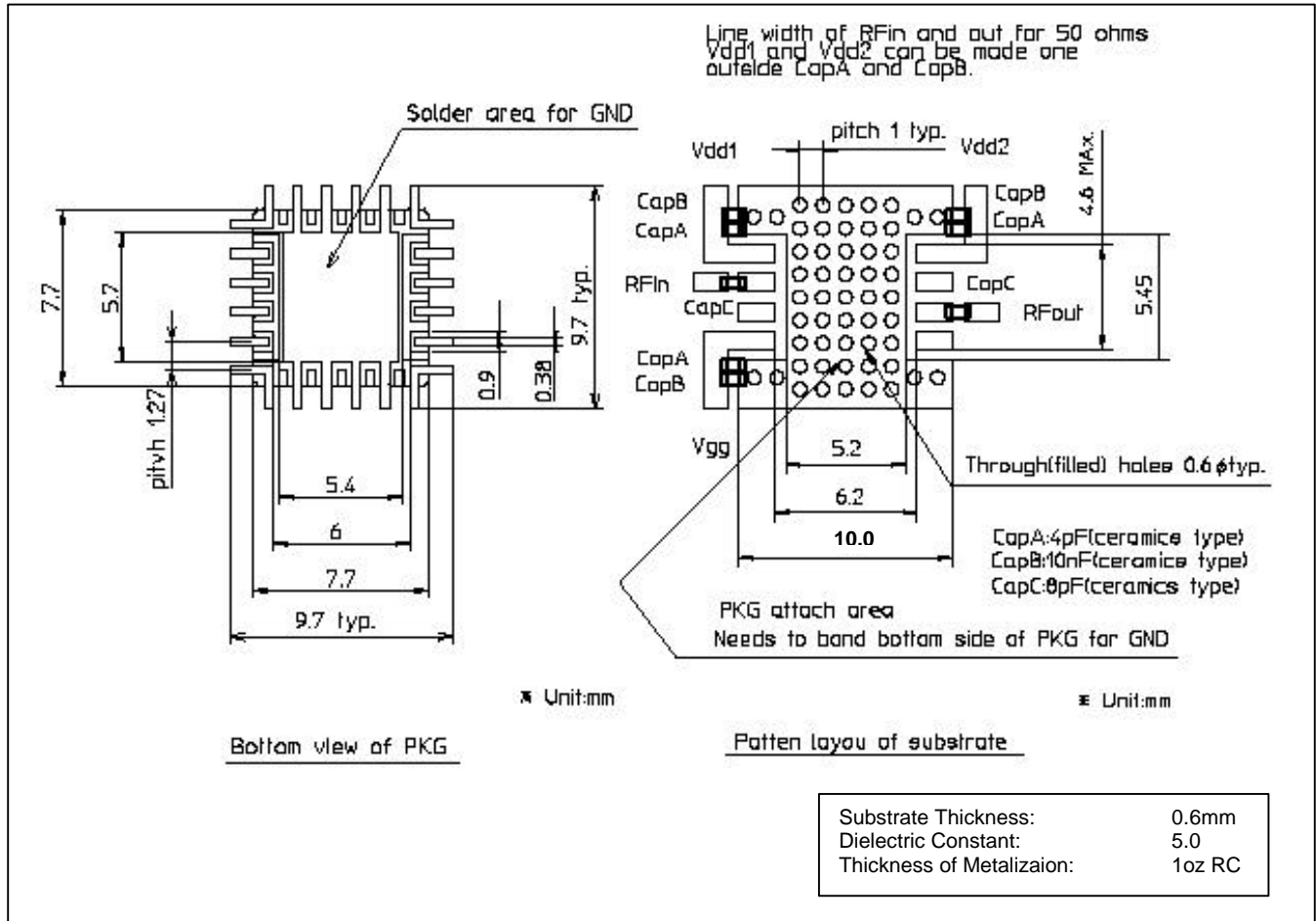
CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Operating Frequency	f		GHz	3.4	—	3.8
Output Power at 1dB Gain Compression Point	P1dB	VDD=7.5V VGG=-5.0V	dBm	29.0	—	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	29.0	—	—
Noise Figure	NF		dB	—	8.0	9.0
Drain Current	IDD	@ Pin=-6dBm	mA	—	500	550
Input Return Loss	—	Small Signal Level	dB	10	—	—
Output Return Loss	—		dB	10	—	—

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Package Outline

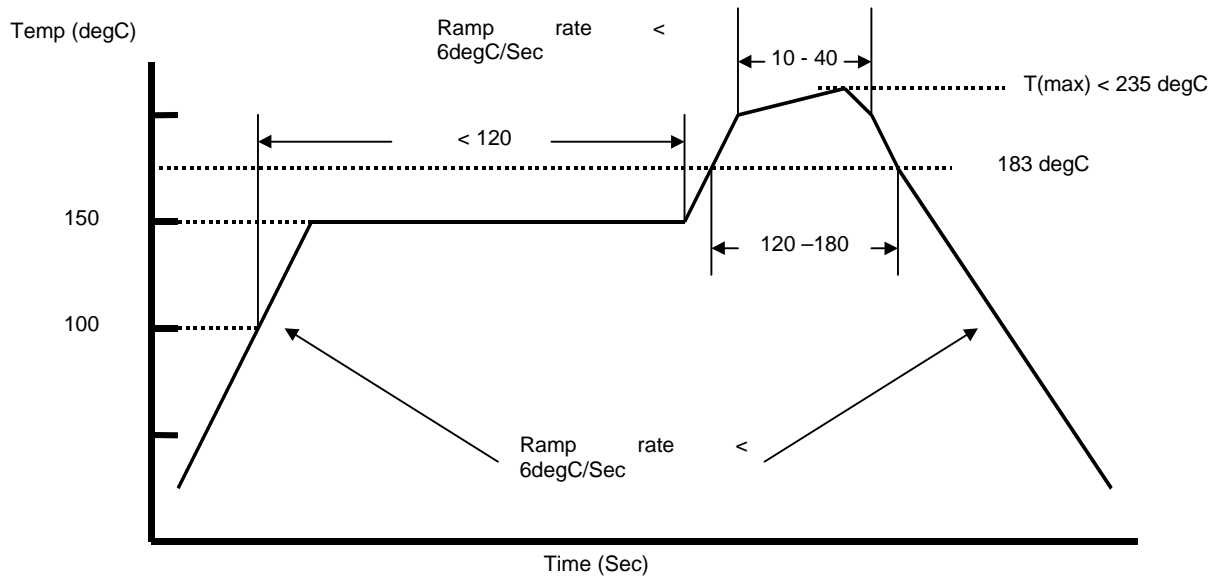


Recommended Bias Configuration



Mounting Recommendation

The backside of this package has to be grounded by soldering. The poor soldering will cause the electrical and thermal performance degradation. Toshiba recommends following reflow soldering profile.



RF Performances

